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J.B. 3/22/02

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Hujanen et al.)	Group Art Unit: 2818
Appl. No.	:	09/997,396)	
Filed	:	November 28, 2001)	
For	:	THIN FILMS FOR MAGNETIC DEVICE)	
Examiner	:	Unknown)	

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PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to examination on the merits, please amend the above-captioned application as indicated below.

IN THE SPECIFICATION:

Please replace paragraph [0057] with the following replacement paragraph:

[0057] Figure 3 depicts a basic two-phase process for atomic layer deposition. Source chemical pulses 440 and 444 are separated from one another in time and space by purge periods 442 and 446. Alternatively, the purge periods can be replaced by evacuation of the chamber to remove byproduct and excess reactant between source chemical pulses 440, 444. Importantly, each pulse preferably has a self-limiting effect, leaving no more than about one molecular monolayer of material per cycle. Typically, the metal source chemicals include ligands that self-terminate adsorption of a monolayer or partial monolayer.

02/20/2002 MWOLDER1 00000128 09997396

01 FC:102
02 FC:103

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18.00 DP